

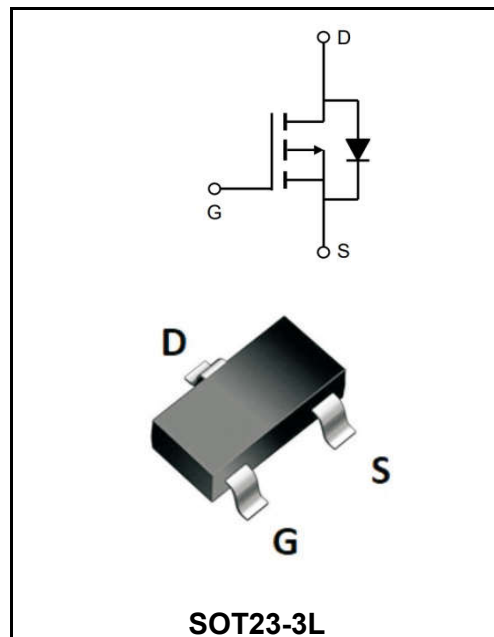
-12V P-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	-7.0A
V_{DSS}	-12V
$R_{DS(on)-typ}(@V_{GS}=-4.5V)$	< 24mΩ (Type:19 mΩ)

Application

- ♦electronic cigarette
- ♦Load switch



Marking Code

YFW2311MI

20P07

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	-12	V
Gate - Source Voltage	V_{GS}	± 12	V
Continuous Drain Current, $V_{GS} @ 10V^1$ @Tc=25°C	I_D	-7.0	A
Continuous Drain Current, $V_{GS} @ 10V^1$ @Tc=100°C	I_D	-3.6	A
Pulsed Drain Current ^{note1}	I_{DM}	-22	A
Power Dissipation @Tc=25°C	P_D	1.6	W
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	125	°C/W
Operating Junction Temperature Range	T_J, T_{STG}	-55 to +150	°C

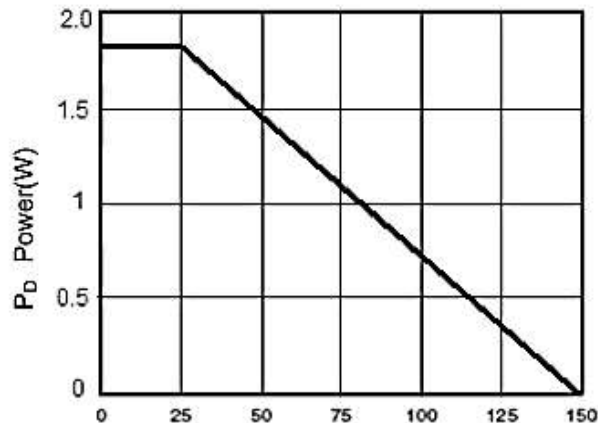
Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	V(BR)DSS	-12	-18	-	V
Zero Gate Voltage Drain Current	$V_{DS}=-12V$, $V_{GS}=0V$	I_{DSS}	-	-	-1	μA
Gate to Body Leakage Current	$V_{GS}=\pm 12V$, $V_{DS}=0V$	I_{GSS}	-	-	± 100	nA
Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu A$	V_{GS(th)}	-0.5	-0.65	-1.0	V
Static Drain-Source on-Resistance note2	$V_{GS}=-4.5V$, $I_D=-5.2A$	R_{DS(ON)}	-	19	24	mΩ
	$V_{GS}=-2.5V$, $I_D=-4.2A$		-	28	35	
Input Capacitance	$V_{DS}=-6V$ $V_{GS}=0V$ $f=1MHz$	C_{iss}	-	1100	-	pF
Output Capacitance		C_{oss}	-	390	-	
Reverse Transfer Capacitance		C_{rss}	-	300	-	
Total Gate Charge	$V_{DS}=-4V$ $I_D=-4.1A$ $V_{GS}=-4.5V$	Q_g	-	11.5	-	nC
Gate-Source Charge		Q_{gs}	-	1.5	-	
Gate-Drain("Miller") Charge		Q_{gd}	-	3.2	-	
Turn-on delay time	$V_{DD}=-4V$ $I_D=-3.3A$ $R_G=1.0\Omega$ $V_{GEN}=-4.5V$ $R_L=1.2\Omega$	t_{d(on)}	-	25	-	ns
Turn-on Rise Time		T_r	-	45	-	
Turn-Off Delay Time		t_{d(OFF)}	-	72	-	
Turn-Off Fall Time		t_f	-	60	-	
Maximum Continuous Drain to Source Diode Forward Current		I_S	-	-	-6.0	A
Maximum Pulsed Drain to Source Diode Forward Current		I_{SM}	-	-	-16	A
Drain to Source Diode Forward Voltage	$V_{GS}=0V$, $I_S=-4.1A$	V_{SD}	-	-	-1.2	V
Reverse Recovery Time	$I_S=-4.1A$, $dI/dt=100A/\mu s$, $V_{GS}=0V$	t_{rr}	-	20	-	ns
Reverse Recovery Charge		Q_{rr}	-	9	-	nC

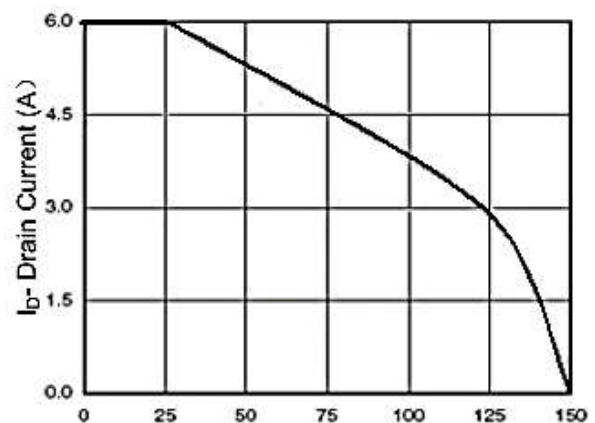
Note :

- 1、The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

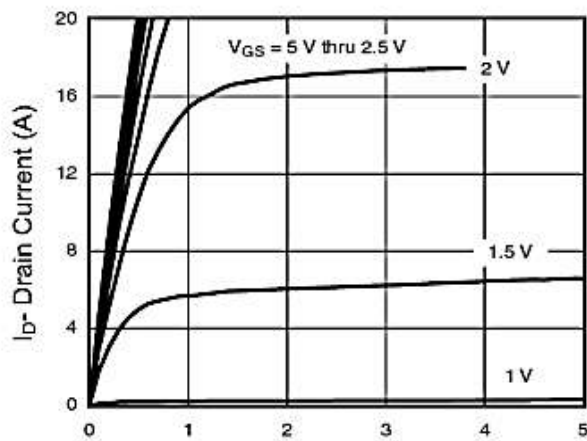
Ratings and Characteristic Curves



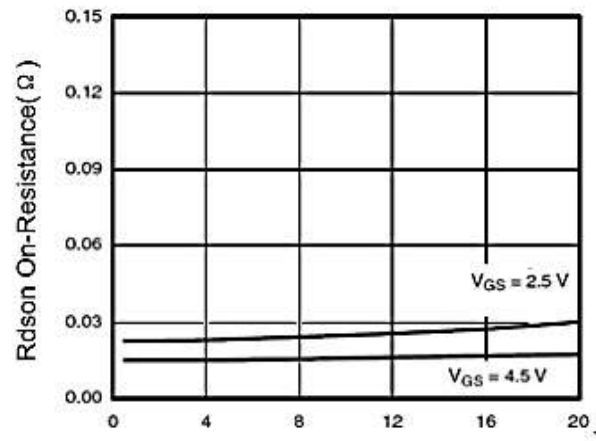
T_J-Junction Temperature(°C)
Figure 1 Power Dissipation



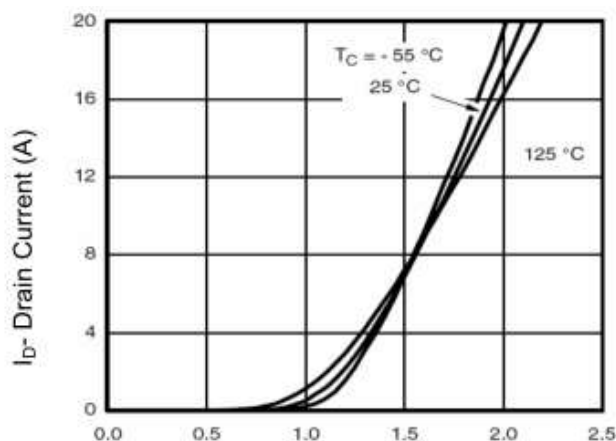
T_J-Junction Temperature(°C)
Figure 2 Drain Current



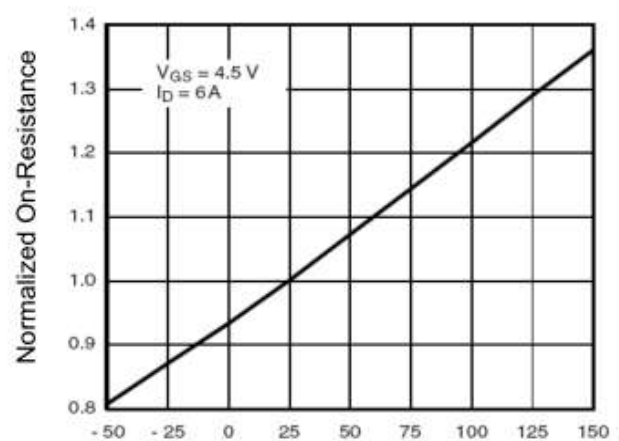
V_{DS} Drain-Source Voltage (V)
Figure 3 Output Characteristics



I_D Drain Current (A)
Figure 4 Drain-Source On-Resistance

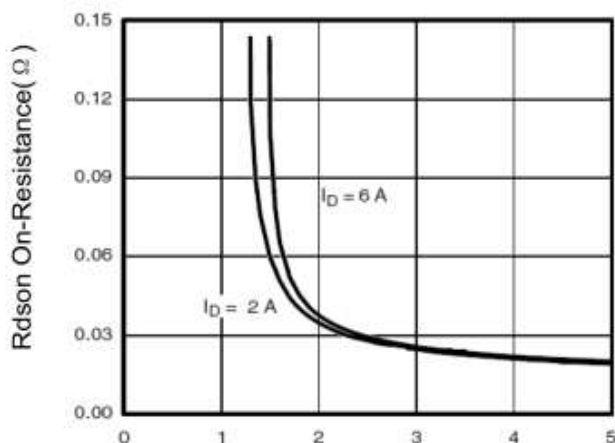


V_{GS} Gate-Source Voltage (V)
Figure 5 Transfer Characteristics

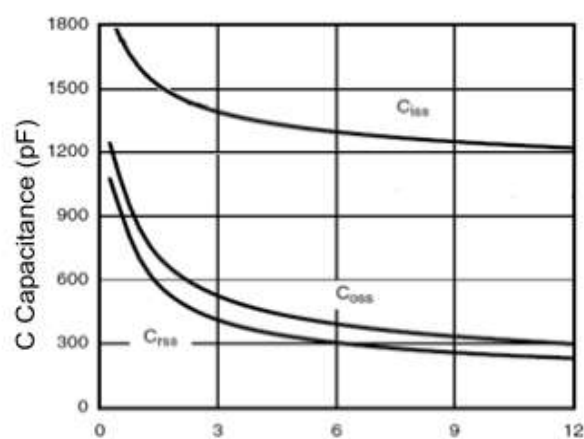


T_J-Junction Temperature(°C)
Figure 6 Drain-Source On-Resistance

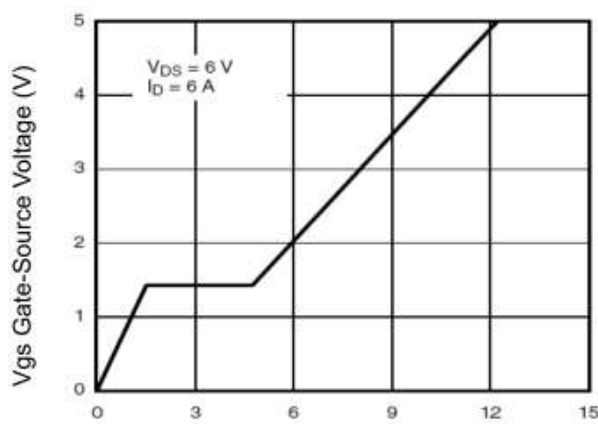
Ratings and Characteristic Curves



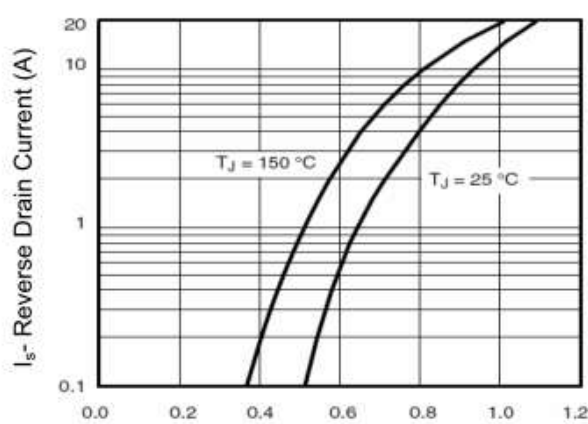
Vgs Gate-Source Voltage (V)
Figure 7 Rdson vs Vgs



Vds Drain-Source Voltage (V)
Figure 8 Capacitance vs Vds



Qg Gate Charge (nC)
Figure 9 Gate Charge



Vsd Source-Drain Voltage (V)
Figure 10 Source-Drain Diode Forward

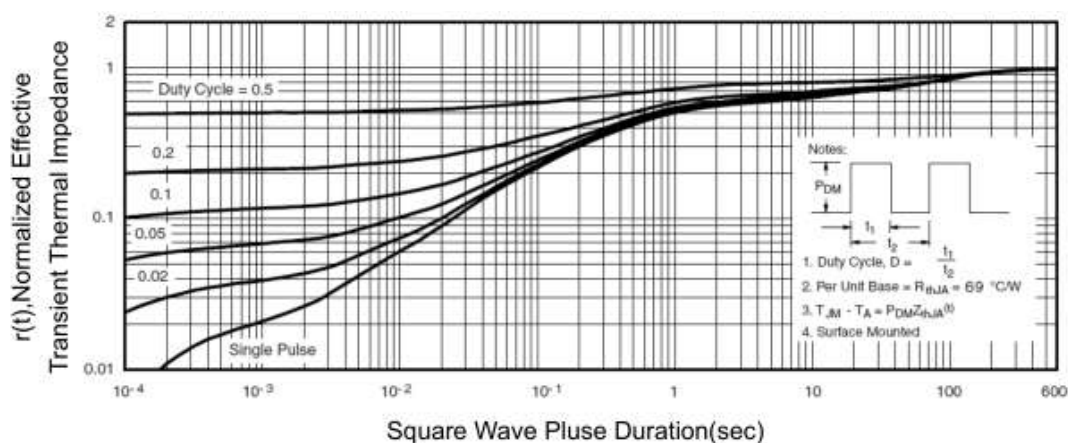


Figure 12 Normalized Maximum Transient Thermal Impedance

Ordering information

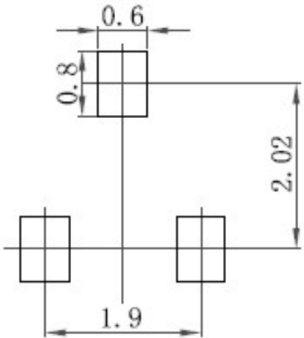
Package	Packing Description	Base Quantity	Packing Quantity
SOT23-3L	Tape/Reel, 7" reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT23-3L

Dim.	Millimeter (mm)		mil	
	Min.	Max.	Min.	Max.
A	1.05	1.25	41	49.2
A1	0.10		3.93	
A2	1.05	1.15	41	45
b	0.30	0.50	12	20
c	0.10	0.20	3.93	7.9
D	2.82	3.02	111	119
E	1.50	1.70	59	67
E1	2.65	2.95	104	116
e	0.95		37.4	
e1	1.80	2.00	71	78
L	0.30	0.066	12	26
Θ	8°			

The recommended mounting pad size



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